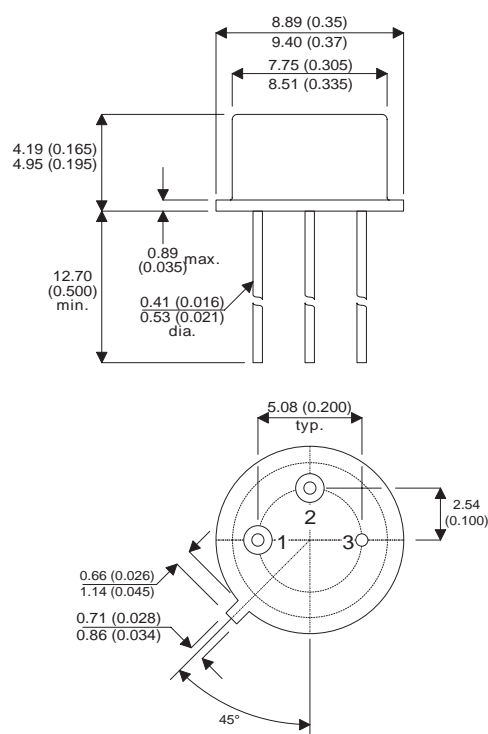


MECHANICAL DATA

Dimensions in mm



TO-5

Pin1 - Emitter

Pin2 - Base

Pin3 - Collector

SMALL SIGNAL PNP TRANSISTORS IN TO-5

APPLICATIONS

Small signal PNP transistors for relay switching resistor logic circuits and general purpose applications.

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

		2N5404	2N5405	2N5406	2N5407
BV_{CBO}	Collector – Base Breakdown Voltage	– 80V	– 100V	– 80V	– 100V
BV_{CEO}	Collector – Emitter Breakdown Voltage	– 80V	– 100V	– 80V	– 100V
BV_{EBO}	Emitter – Base Breakdown Voltage	– 6V	– 6V	– 6V	– 6V
$I_{C(Max)}$	Collector Current	– 5A	– 5A	– 5A	– 5A
$I_{B(Max)}$	Base Current	– 2A	– 2A	– 2A	– 2A
P_{TOT}	Total Power Dissipation (100°C Case)	5W	5W	5W	5W
T_{STG}, T_J	Operating and Storage Temperature Range	– 65°C to +200°C			

Semelab Plc reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.

ELECTRICAL CHARACTERISTICS (T_{case} = 25°C unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I _{CEX} Collector Cut-Off Current	V _{CE} = BV _{CEO} V _{BE} = 1.5V V _{CE} = BV _{CEO} V _{BE} = 1.5V T _C = 150°C			- 10 - 500	μA
V _{CEO(SUS)} Collector-Emitter Sustaining Voltage With Base Open	I _C = -100mA I _B = 0 2N5404 2N5406	-80			V
	I _C = -100mA I _B = 0 2N5405 2N5407	-100			
I _{CEO} Collector Cut-Off Current	V _{CE} = - 50V I _C = 0	-100			μA
I _{EBO}	V _{EB} = - 4V I _C = 0			-1	μA
h _{FE} Common Emitter, Small-Signal Value of the Short-Circuit Forward Current Transfer Ratio (f = 1KHz)	I _C = - 2A V _{CE} = - 5V 2N5404 2N5405	20		60	-
	I _C = - 2A V _{CE} = - 5V 2N5406 2N5407	40		120	
V _{CE(SAT)} Collector-Emitter Saturation Voltage	I _C = - 2A I _B = - 0.2A			-0.6	V
V _{BE(SAT)} Base-Emitter Saturation Voltage	I _C = - 2A I _B = - 0.2A			-1.2	V
DYNAMIC CHARACTERISTICS					
C _{OBO} Collector Base Capacitance	V _{CB} = - 10V f = 1MHz			150	pf
f _t Transistion Frequency	V _{CE} = - 5V I _C = - 0.2A	40			MHz
t _r Rise Time	I _C = - 2A I _{B1} = - I _{B2} = 0.2A			0.5	μ
t _s Storage time	I _C = - 2A 2N5404 I _{B1} = - I _{B2} = 0.2A 2N5405			0.75	μ
	I _C = - 2A 2N5406 I _{B1} = - I _{B2} = 2A 2N5407			1	
t _f Fall Time	I _C = -2A 2N5404 I _{B1} = - I _{B2} = 2A 2N5405			0.2	μ
	I _C = -2A 2N5406 I _{B1} = - I _{B2} = 2A 2N5407			0.3	

* Pulse test : Pulse Width < 300μs ,Duty Cycle < 2%